

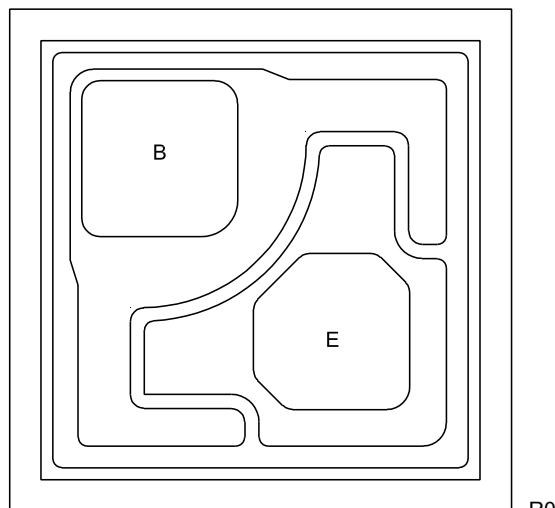
PROCESS CP792V
Small Signal Transistor
PNP - Amp/Switch Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.0 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	3.7 x 3.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

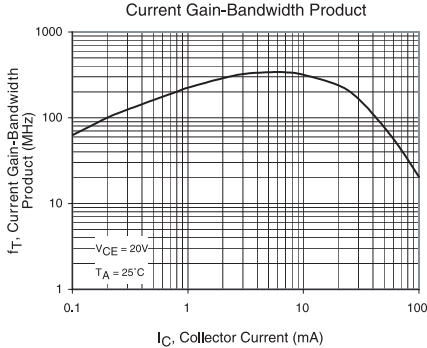
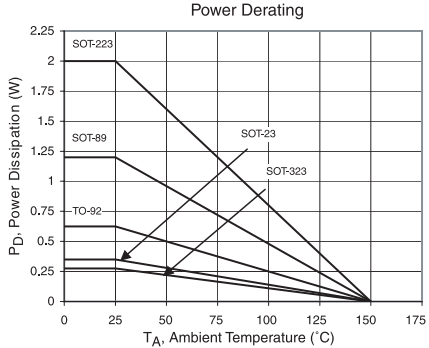
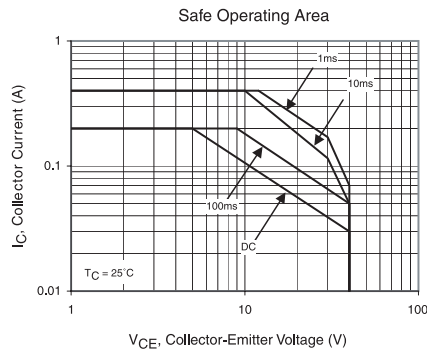
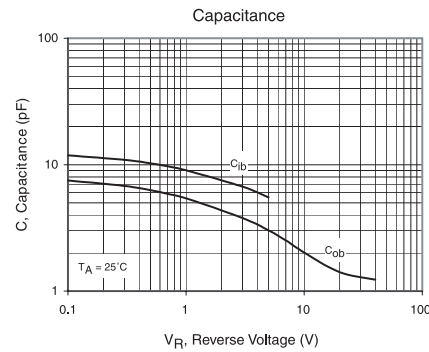
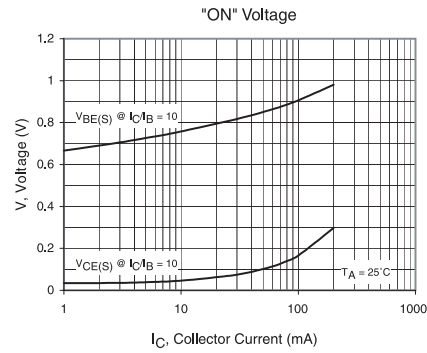
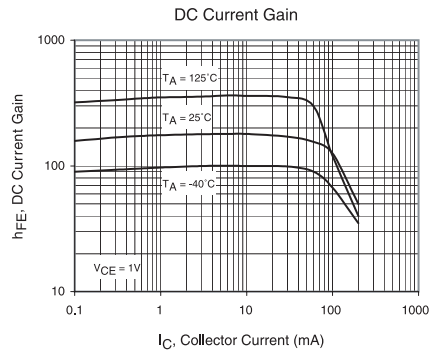
93,826

PRINCIPAL DEVICE TYPES

2N3906
CMKT3906
CMLT3906E
CMPT3906
CMPT3906E
CMST3906
CXT3906
CZT3906

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R1 (15 -April 2005)



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